74LVC2G06

Inverters with open-drain outputs

Rev. 03 — 21 May 2007 Product data sheet

1. General description

The 74LVC2G06 provides two inverting buffers.

The output of this device is an open drain and can be connected to other open-drain outputs to implement active-LOW wired-OR or active-HIGH wired-AND functions.

Input can be driven from either 3.3 V or 5 V devices. This feature allows the use of this device in a mixed 3.3 V and 5 V environment.

Schmitt trigger action at all inputs makes the circuit tolerant for slower input rise and fall time.

This device is fully specified for partial power-down applications using I_{OFF}. The I_{OFF} circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

2. Features

- Wide supply voltage range from 1.65 V to 5.5 V
- 5 V tolerant input/output for interfacing with 5 V logic
- High noise immunity
- Complies with JEDEC standard:
  - JESD8-7 (1.65 V to 1.95 V)
  - JESD8-5 (2.3 V to 2.7 V)
  - JESD8-B/JESD36 (2.7 V to 3.6 V)
- ESD protection:
  - HBM JESD22-A114E exceeds 2000 V
  - MM JESD22-A115-A exceeds 200 V
- –24 mA output drive (V_{CC} = 3.0 V)
- CMOS low power consumption
- Latch-up performance exceeds 250 mA
- Direct interface with TTL levels
- Inputs accept voltages up to 5 V
- Multiple package options
- Specified from –40 °C to +85 °C and –40 °C to +125 °C

3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74LVC2G06GW	–40 °C to +125 °C	SC-88	plastic surface-mounted package; 6 leads	SOT363
74LVC2G06GV	–40 °C to +125 °C	TSOP6	plastic surface-mounted package (TSOP6); 6 leads	SOT457
74LVC2G06GM	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 × 1.45 × 0.5 mm	SOT886
74LVC2G06GF	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 × 1 × 0.5 mm	SOT891

4. Marking

Table 2. Marking

Type number	Marking code
74LVC2G06GW	V6
74LVC2G06GV	V06
74LVC2G06GM	V6
74LVC2G06GF	V6

5. Functional diagram

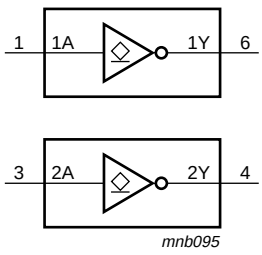


Fig 1. Logic symbol

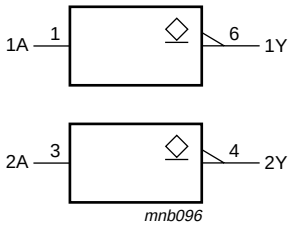


Fig 2. IEC logic symbol

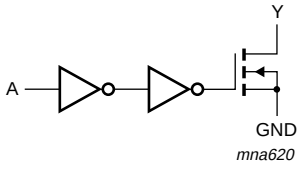


Fig 3. Logic diagram (one driver)

6. Pinning information

6.1 Pinning

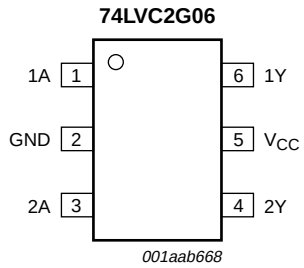


Fig 4. Pin configuration SOT363 and SOT457

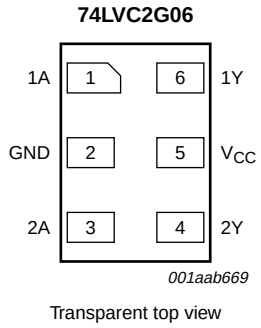


Fig 5. Pin configuration SOT886

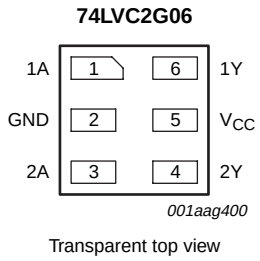


Fig 6. Pin configuration SOT891

6.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
1A	1	data input
GND	2	ground (0 V)
2A	3	data input
2Y	4	data output
V_{CC}	5	supply voltage
1Y	6	data output

7. Functional description

Table 4. Function table[1]

Input nA	Output nY
L	Z
H	L

[1] H = HIGH voltage level;
L = LOW voltage level;
Z = high-impedance OFF-state.

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CC}	supply voltage			–0.5	+6.5	V
I_{IK}	input clamping current	$V_I < 0$ V		–50	-	mA
V_I	input voltage		[1]	–0.5	+6.5	V
I_{OK}	output clamping current	$V_O < 0$ V		–50	-	mA
V_O	output voltage	Active mode	[1]	–0.5	+6.5	V
		Power-down mode	[1][2]	–0.5	+6.5	V
I_O	output current	V_O = 0 V to 6.5 V		-	50	mA
I_{CC}	supply current			-	100	mA
I_{GND}	ground current			–100	-	mA
T_{stg}	storage temperature			–65	+150	°C
P_{tot}	total power dissipation	T_{amb} = –40 °C to +125 °C	[3]	-	250	mW

[1] The minimum input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] When V_{CC} = 0 V (Power-down mode), the output voltage can be 5.5 V in normal operation.

[3] For SC-88 and SC-74 packages: above 87.5 °C the value of P_{tot} derates linearly with 4.0 mW/K.
For XSON6 packages: above 45 °C the value of P_{tot} derates linearly with 2.4 mW/K.

9. Recommended operating conditions

Table 6. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{CC}	supply voltage		1.65	-	5.5	V
V_I	input voltage		0	-	5.5	V
V_O	output voltage	Active mode	0	-	5.5	V
		Power-down mode; V_{CC} = 0 V	0	-	5.5	V
T_{amb}	ambient temperature		–40	-	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	V_{CC} = 1.65 V to 2.7 V	-	-	20	ns/V
		V_{CC} = 2.7 V to 5.5 V	-	-	10	ns/V

10. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
T_{amb} = −40 °C to +85 °C	[1]						
V_{IH}	HIGH-level input voltage	V_{CC} = 1.65 V to 1.95 V		0.65 × V_{CC}	-	-	V
		V_{CC} = 2.3 V to 2.7 V		1.7	-	-	V
		V_{CC} = 2.7 V to 3.6 V		2.0	-	-	V
		V_{CC} = 4.5 V to 5.5 V		0.7 × V_{CC}	-	-	V
V_{IL}	LOW-level input voltage	V_{CC} = 1.65 V to 1.95 V		-	-	0.35 × V_{CC}	V
		V_{CC} = 2.3 V to 2.7 V		-	-	0.7	V
		V_{CC} = 2.7 V to 3.6 V		-	-	0.8	V
		V_{CC} = 4.5 V to 5.5 V		-	-	0.3 × V_{CC}	V
V_{OL}	LOW-level output voltage	V_I = V_{IH} or V_{IL}					
		I_O = 100 µA; V_{CC} = 1.65 V to 5.5 V		-	-	0.1	V
		I_O = 4 mA; V_{CC} = 1.65 V		-	-	0.45	V
		I_O = 8 mA; V_{CC} = 2.3 V		-	-	0.3	V
		I_O = 12 mA; V_{CC} = 2.7 V		-	-	0.4	V
		I_O = 24 mA; V_{CC} = 3.0 V		-	-	0.55	V
		I_O = 32 mA; V_{CC} = 4.5 V		-	-	0.55	V
I_I	input leakage current	V_I = 5.5 V or GND; V_{CC} = 0 V to 5.5 V	[2]	-	±0.1	±5	µA
I_{OZ}	OFF-state output current	V_I = V_{IH} or V_{IL}; V_O = V_{CC} or GND; V_{CC} = 5.5 V		-	±0.1	±10	µA
I_{OFF}	power-off leakage current	V_I or V_O = 5.5 V; V_{CC} = 0 V		-	±0.1	±10	µA
I_{CC}	supply current	V_I = 5.5 V or GND; I_O = 0 A; V_{CC} = 1.65 V to 5.5 V		-	0.1	10	µA
ΔI_{CC}	additional supply current	per pin; V_I = V_{CC} − 0.6 V; I_O = 0 A; V_{CC} = 2.3 V to 5.5 V	[2]	-	5	500	µA
C_I	input capacitance			-	2.5	-	pF

Table 7. Static characteristics *…continued*

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
T_{amb} = −40 °C to +125 °C						
V_{IH}	HIGH-level input voltage	V_{CC} = 1.65 V to 1.95 V	0.65 × V_{CC}	-	-	V
		V_{CC} = 2.3 V to 2.7 V	1.7	-	-	V
		V_{CC} = 2.7 V to 3.6 V	2.0	-	-	V
		V_{CC} = 4.5 V to 5.5 V	0.7 × V_{CC}	-	-	V
V_{IL}	LOW-level input voltage	V_{CC} = 1.65 V to 1.95 V	-	-	0.35 × V_{CC}	V
		V_{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		V_{CC} = 2.7 V to 3.6 V	-	-	0.8	V
		V_{CC} = 4.5 V to 5.5 V	-	-	0.3 × V_{CC}	V
V_{OL}	LOW-level output voltage	V_I = V_{IH} or V_{IL}				
		I_O = 100 µA; V_{CC} = 1.65 V to 5.5 V	-	-	0.10	V
		I_O = 4 mA; V_{CC} = 1.65 V	-	-	0.70	V
		I_O = 8 mA; V_{CC} = 2.3 V	-	-	0.45	V
		I_O = 12 mA; V_{CC} = 2.7 V	-	-	0.60	V
		I_O = 24 mA; V_{CC} = 3.0 V	-	-	0.80	V
		I_O = 32 mA; V_{CC} = 4.5 V	-	-	0.80	V
I_I	input leakage current	V_I = 5.5 V or GND; V_{CC} = 0 V to 5.5 V	-	-	±20	µA
I_{OZ}	OFF-state output current	V_I = V_{IH} or V_{IL}; V_O = V_{CC} or GND; V_{CC} = 5.5 V	-	-	±10	µA
I_{OFF}	power-off leakage current	V_I or V_O = 5.5 V; V_{CC} = 0 V	-	-	±20	µA
I_{CC}	supply current	V_I = 5.5 V or GND; I_O = 0 A; V_{CC} = 1.65 V to 5.5 V	-	-	40	µA
ΔI_{CC}	additional supply current	per pin; V_I = V_{CC} − 0.6 V; I_O = 0 A; V_{CC} = 2.3 V to 5.5 V	-	-	5000	µA

[1] All typical values are measured at T_{amb} = 25 °C.

[2] These typical values are measured at V_{CC} = 3.3 V.

11. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V). For test circuit see Figure 8.

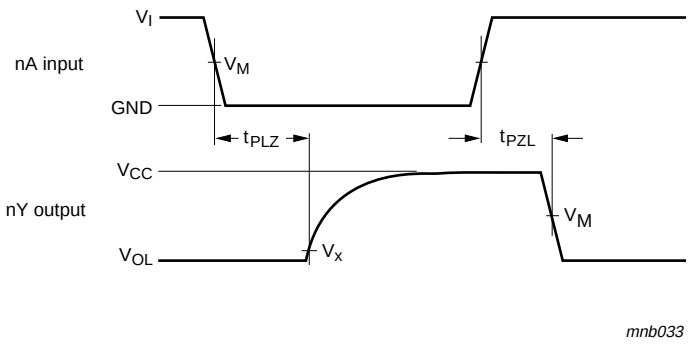
Symbol	Parameter	Conditions		–40 °C to +85 °C			–40 °C to +125 °C		Unit
				Min	Typ[1]	Max	Min	Max	
t_{pd}	propagation delay	nA to nY; see Figure 7	[2]						
		V_{CC} = 1.65 V to 1.95 V		1.0	3.2	6.5	1.0	8.2	ns
		V_{CC} = 2.3 V to 2.7 V		0.5	2.0	3.9	0.5	4.9	ns
		V_{CC} = 2.7 V		1.0	2.6	4.2	1.0	5.3	ns
		V_{CC} = 3.0 V to 3.6 V		0.5	2.3	3.4	0.5	4.3	ns
		V_{CC} = 4.5 V to 5.5 V		0.5	1.6	2.9	0.5	3.7	ns
C_{PD}	power dissipation capacitance	V_I = GND to V_{CC}; V_{CC} = 3.3 V	[3]	-	5.9	-	-	-	pF

[1] Typical values are measured at T_{amb} = 25 °C and V_{CC} = 1.8 V, 2.5 V, 2.7 V, 3.3 V and 5.0 V respectively.

[2] t_{pd} is the same as t_{PLZ} and t_{PZL}.

[3] C_{PD} is used to determine the dynamic power dissipation (P_D in µW).
$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$ where:
f_i = input frequency in MHz;
f_o = output frequency in MHz;
C_L = output load capacitance in pF;
V_{CC} = supply voltage in V;
N = number of inputs switching;
$\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of outputs.

12. Waveforms



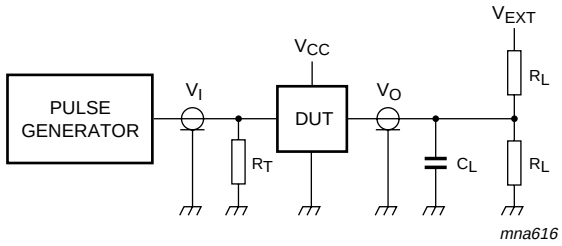
Measurement points are given in Table 9.

V_{OL} is the typical output voltage drop that occur with the output load.

Fig 7. The input (nA) to output (nY) propagation delays

Table 9. Measurement points

Supply voltage	Input	Output	
V_{CC}	V_M	V_M	V_X
1.65 V to 1.95 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$	V_{OL} + 0.15 V
2.3 V to 2.7 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$	V_{OL} + 0.15 V
2.7 V	1.5 V	1.5 V	V_{OL} + 0.3 V
3.0 V to 3.6 V	1.5 V	1.5 V	V_{OL} + 0.3 V
4.5 V to 5.5 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$	V_{OL} + 0.3 V



Test data is given in Table 10.

Definitions for test circuit:

R_L = Load resistance.

C_L = Load capacitance including jig and probe capacitance.

R_T = Termination resistance should be equal to the output impedance Z_o of the pulse generator.

V_{EXT} = External voltage for measuring switching times.

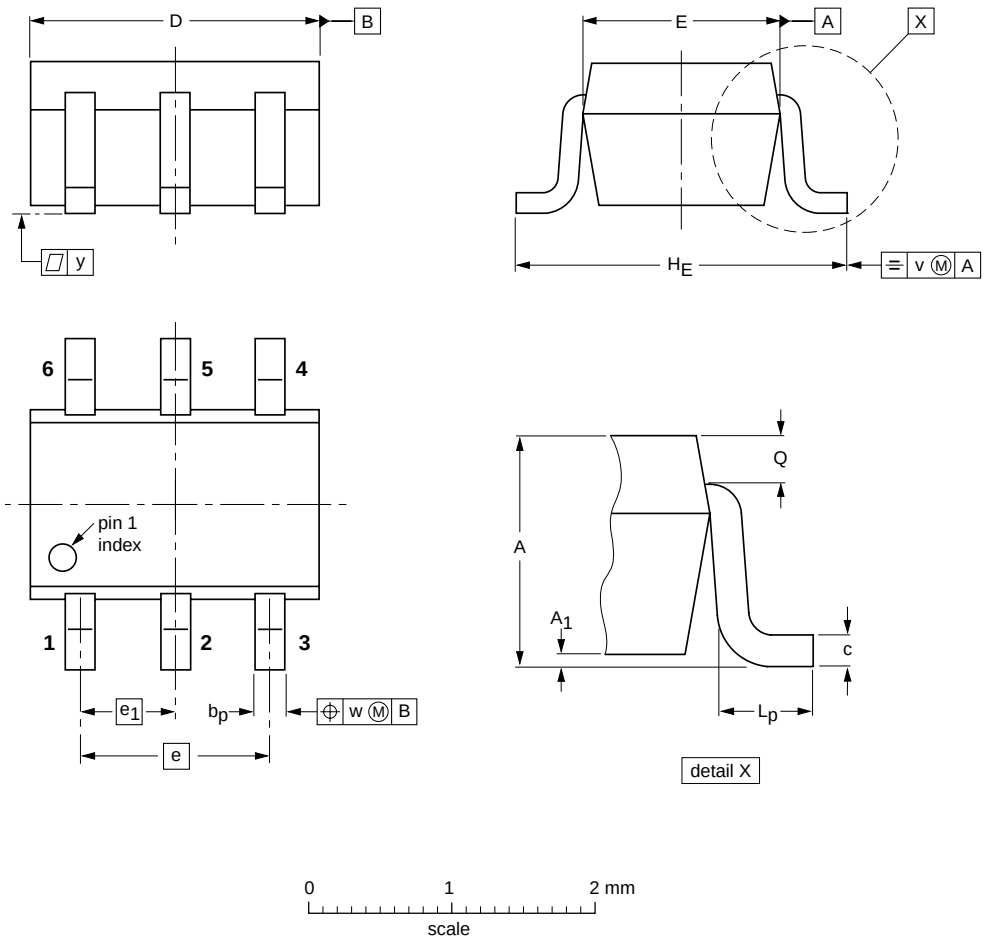
Fig 8. Load circuitry for switching times

Table 10. Test data

Supply voltage	Input		Load		V_{EXT}
V_{CC}	V_I	t_r, t_f	C_L	R_L	t_{PZL}, t_{PLZ}
1.65 V to 1.95 V	V_{CC}	≤ 2.0 ns	30 pF	1 kΩ	$2 \times V_{CC}$
2.3 V to 2.7 V	V_{CC}	≤ 2.0 ns	30 pF	500 Ω	$2 \times V_{CC}$
2.7 V	2.7 V	≤ 2.5 ns	50 pF	500 Ω	6 V
3.0 V to 3.6 V	2.7 V	≤ 2.5 ns	50 pF	500 Ω	6 V
4.5 V to 5.5 V	V_{CC}	≤ 2.5 ns	50 pF	500 Ω	$2 \times V_{CC}$

13. Package outline

Plastic surface-mounted package; 6 leads **SOT363**



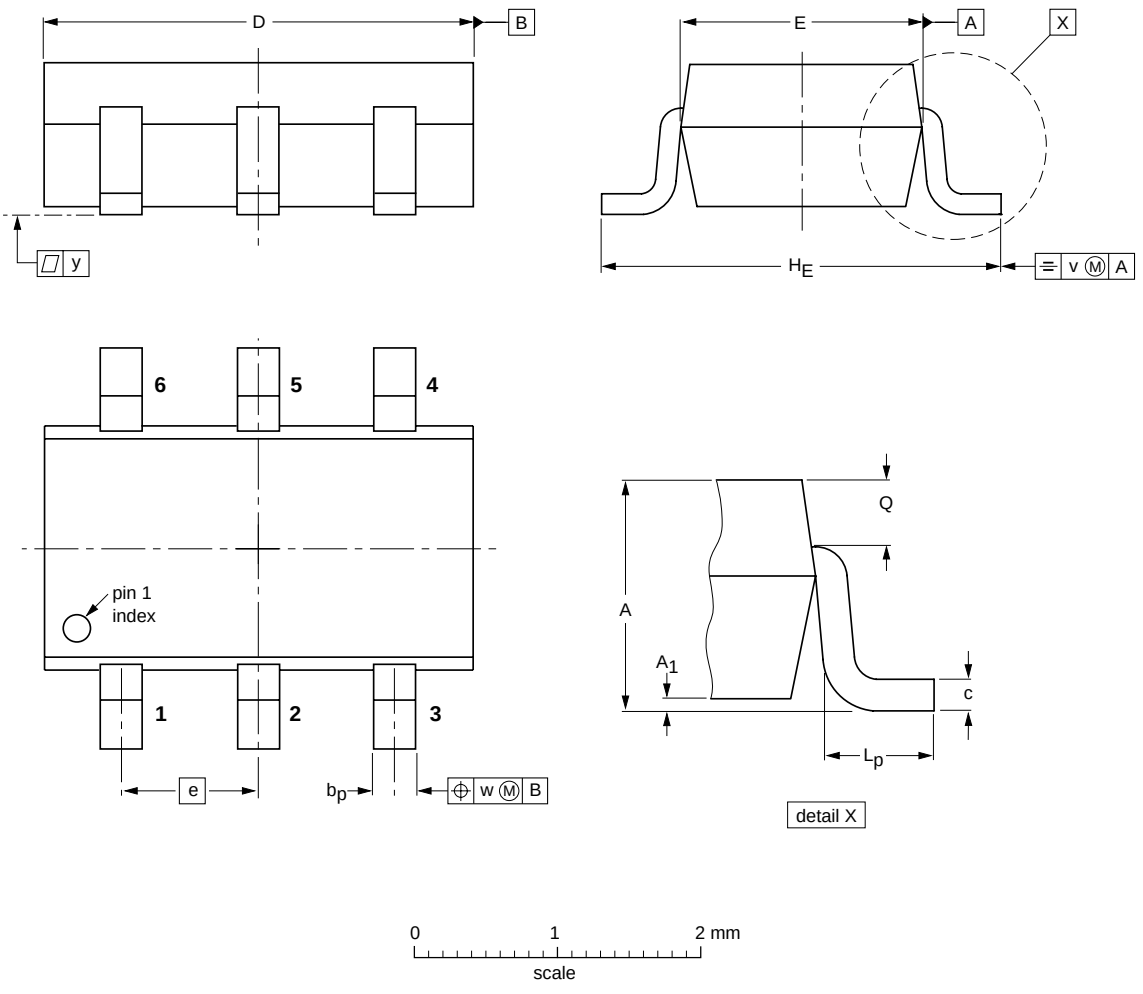
DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1 max	b_p	c	D	E	e	e_1	H_E	L_p	Q	v	w	y
mm	1.1 0.8	0.1	0.30 0.20	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.25 0.15	0.2	0.2	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT363			SC-88			~~04-11-08~~ 06-03-16

Fig 9. Package outline SOT363 (SC-88)

Plastic surface-mounted package (TSOP6); 6 leads **SOT457**



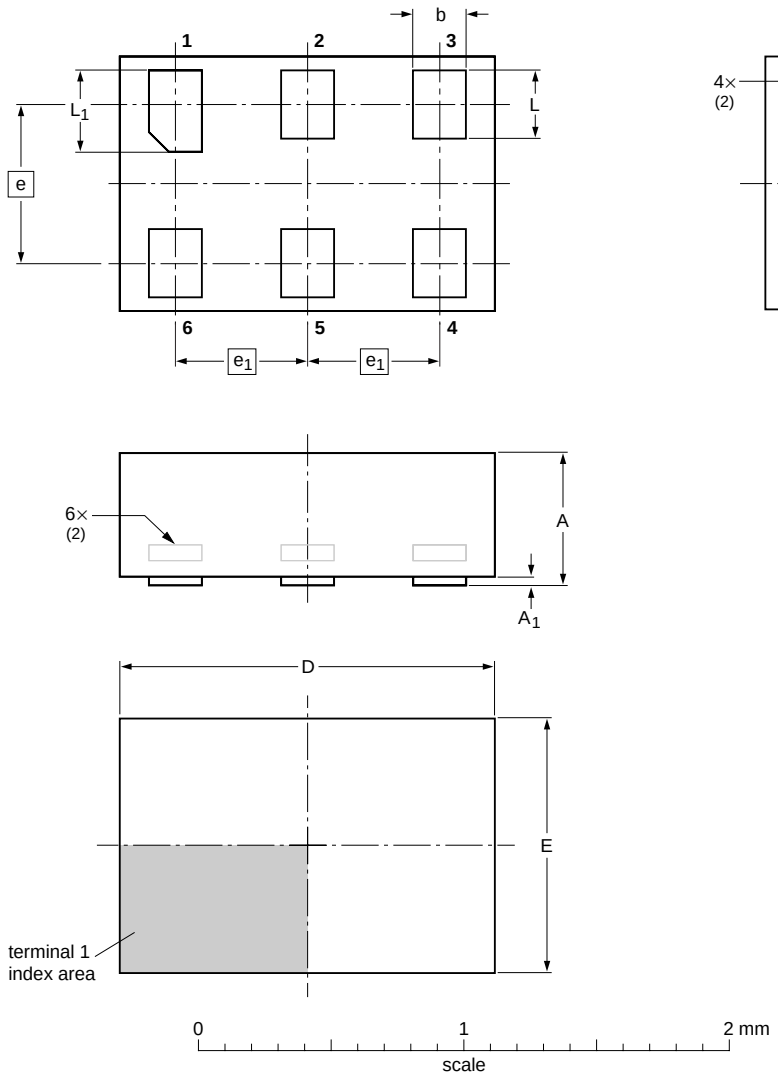
DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1	b_p	c	D	E	e	H_E	L_p	Q	v	w	y
mm	1.1 0.9	0.1 0.013	0.40 0.25	0.26 0.10	3.1 2.7	1.7 1.3	0.95	3.0 2.5	0.6 0.2	0.33 0.23	0.2	0.2	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT457			SC-74			~~05-11-07~~ 06-03-16

Fig 10. Package outline SOT457 (TSOP6)

XSON6: plastic extremely thin small outline package; no leads; 6 terminals; body 1 x 1.45 x 0.5 mm **SOT886**



DIMENSIONS (mm are the original dimensions)

UNIT	A(1) max	A1 max	b	D	E	e	e1	L	L1
mm	0.5	0.04	0.25 0.17	1.5 1.4	1.05 0.95	0.6	0.5	0.35 0.27	0.40 0.32

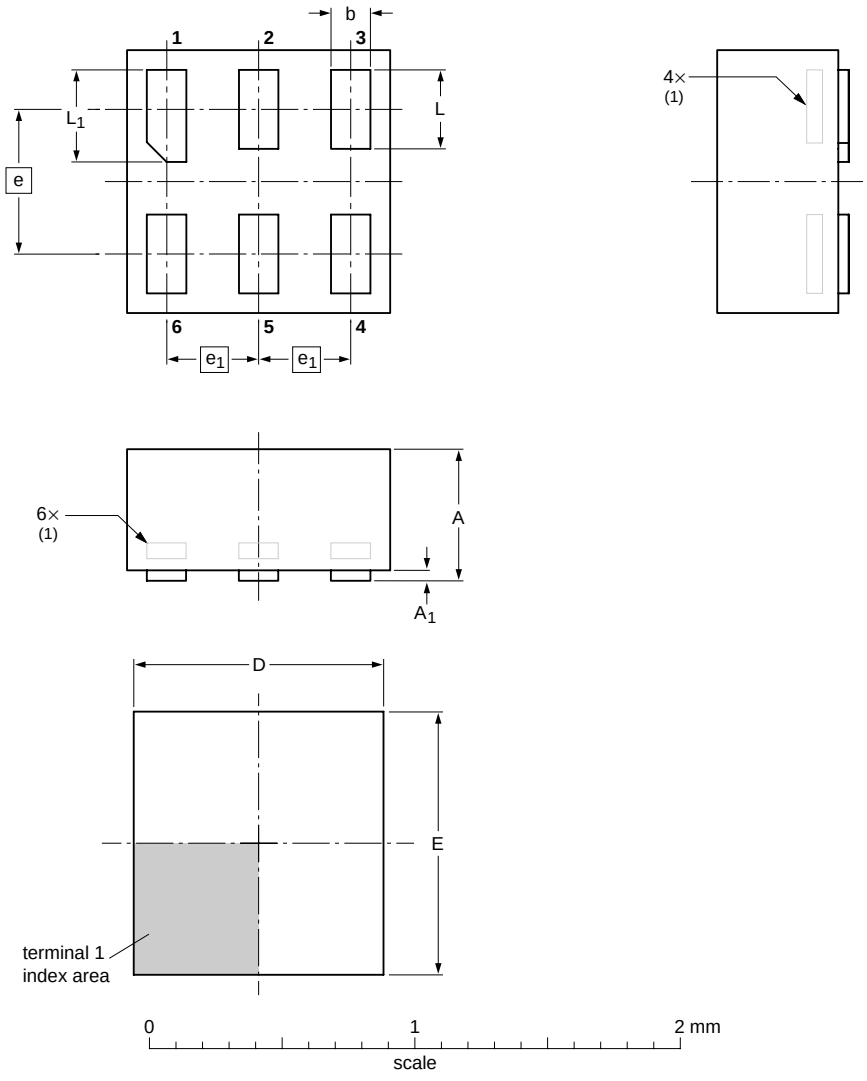
Notes

1. Including plating thickness.
2. Can be visible in some manufacturing processes.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT886		MO-252				~~04-07-15~~ 04-07-22

Fig 11. Package outline SOT886 (XSON6)

XSON6: plastic extremely thin small outline package; no leads; 6 terminals; body 1 x 1 x 0.5 mm **SOT891**



DIMENSIONS (mm are the original dimensions)

UNIT	A max	A_1 max	b	D	E	e	e_1	L	L_1
mm	0.5	0.04	0.20 0.12	1.05 0.95	1.05 0.95	0.55	0.35	0.35 0.27	0.40 0.32

Note

1. Can be visible in some manufacturing processes.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT891						~~05-04-06~~ 07-05-15

Fig 12. Package outline SOT891 (XSON6)

14. Abbreviations

Table 11. Abbreviations

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

15. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74LVC2G06_3	20070521	Product data sheet	-	74LVC2G06_2
Modifications:	• The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. • Legal texts have been adapted to the new company name where appropriate. • Added type number 74LVC2G06GF (XSON6/SOT891 package). • Section 10 “Static characteristics”: Changed: Conditions for input leakage and supply current.			
74LVC2G06_2	20040910	Product data sheet	-	74LVC2G06_1
74LVC2G06_1	20030825	Product data sheet	-	-

16. Legal information

16.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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17. Contact information

For additional information, please visit: **http://www.nxp.com**

For sales office addresses, send an email to: **salesaddresses@nxp.com**

18. Contents

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